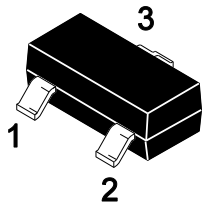
1SS193
Silicon Epitaxial Planar Switching Diode

Features

- Low Forward Voltage
- Fast Recovery Time

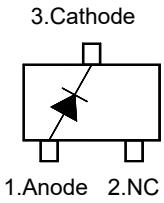
SOT-23



1.Anode 2.NC 3.Cathode

Marking Code : F3

Equivalent Circuit



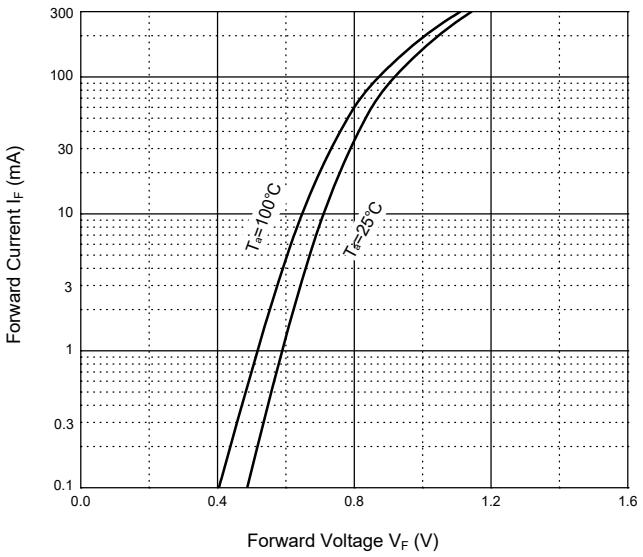
Absolute Maximum Ratings (T_A=25℃)

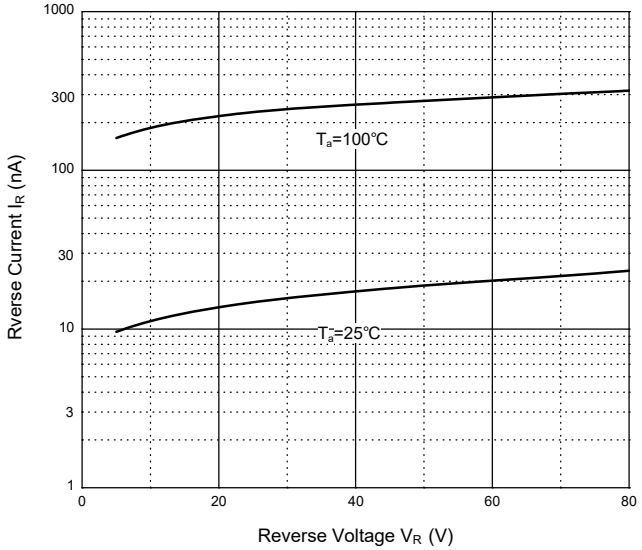
Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current (10 ms)	I_{FSM}	2	A
Maximum Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

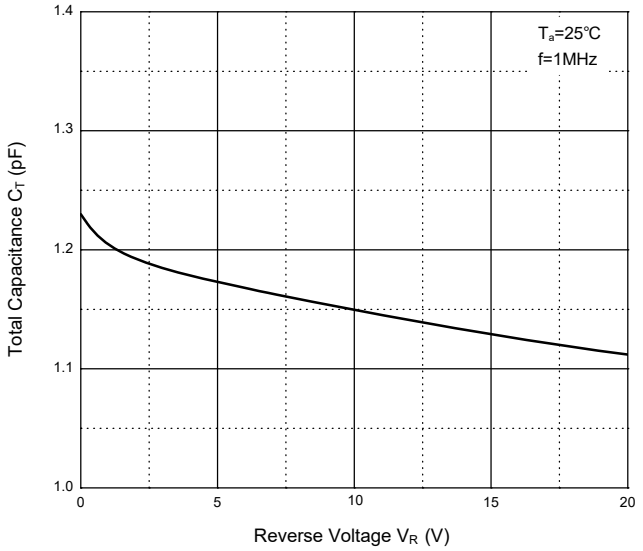
Electrical Characteristics (T_A=25℃)

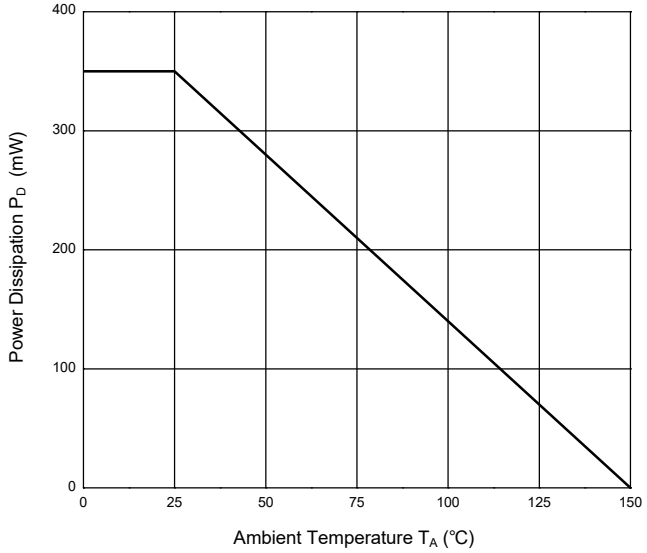
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 100 mA	V_F	 0.6 0.72 0.9	 -- -- 1.2	V
Reverse Current at V_R = 20 V at V_R = 75 V	I_R	 -- --	 0.1 0.5	μA
Typical Junction Capacitance at V_R = 0 V, f = 1 MHz	C_j	--	4	pF
Maximum Reverse Recovery Time at I_F = 10 mA, V_R = 6 V, I_{RR} = 1 mA, R_L = 100 Ω	T_{rr}	--	4	nS

Typical Characteristic Curves





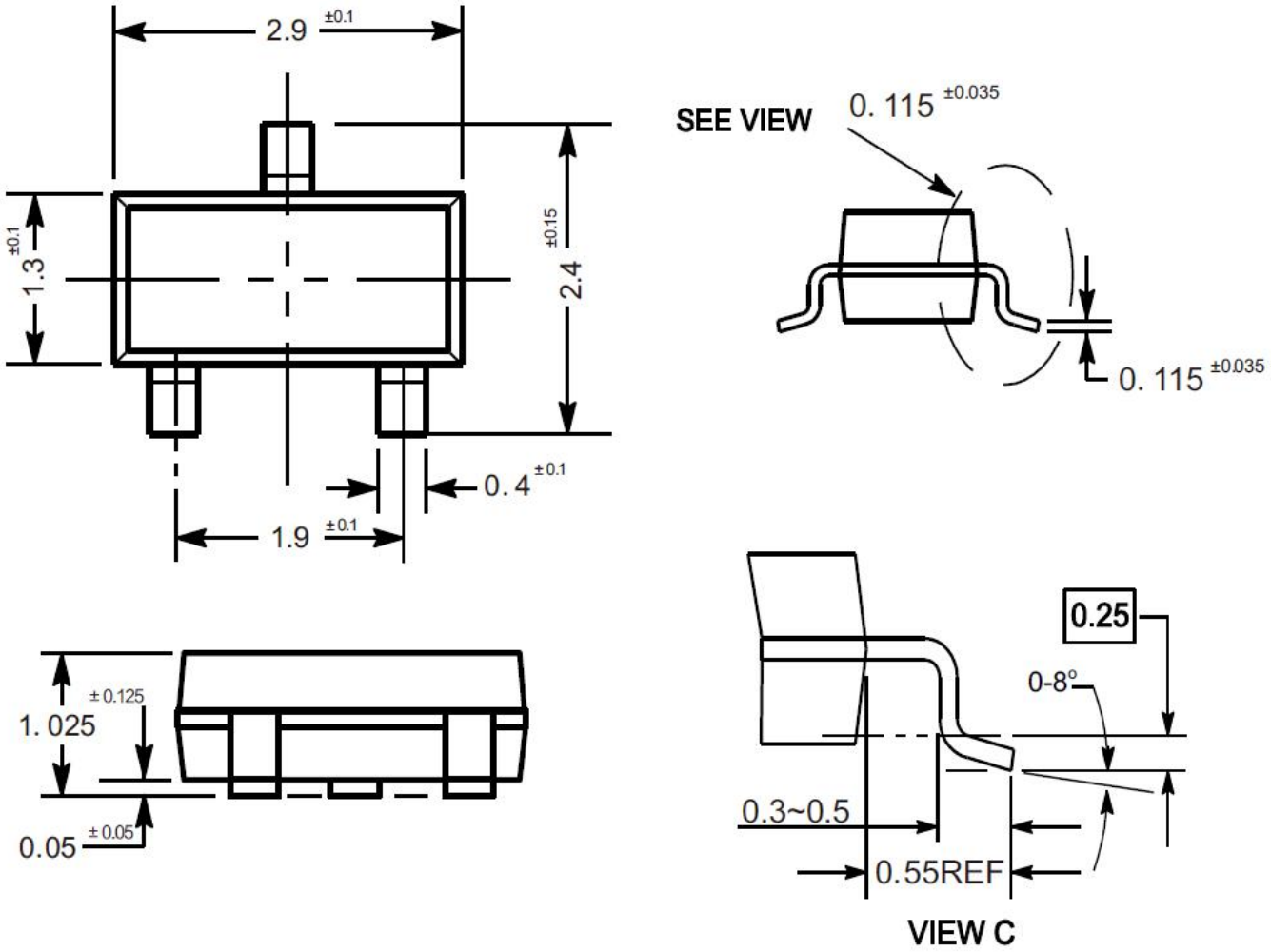




Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
1SS193	SOT-23	3,000PCS/Reel&7inches